

## **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

# **IRFR120N, IIRFR120N**

#### FEATURES Static drain-source on-resistance: Ros(on)≤210mΩ · Enhancement mode: 100% avalanche tested Minimum Lot-to-Lot variations for robust device performance and reliable operation pin 1, Gate 2, Drain DPAK 3, Source DESCRITION TO-252 Package · Fast switching C 0.5 ABSOLUTE MAXIMUM RATINGS(Ta=25°C) K SYMBOL VALUE UNIT PARAMETER C VDSS Drain-Source Voltage 100 V D V<sub>GS</sub> Gate-Source Voltage $\pm 20$ V Drain Current-Continuous 9.4 ΙD А 3.0 Drain Current-Single Pulsed 38 А **I**DM F $\mathbf{P}_{\mathsf{D}}$ Total Dissipation @Tc=25°C W 48 G H H Max. Operating Junction Temperature °C Τį 175 mm Storage Temperature -55~175 °C Tstg MAX DIM MIN 6.40 6.60 А 5.20 5.40 В THERMAL CHARACTERISTICS 1.15 35 D 5. 70 6. 10 SYMBOL PARAMETER MAX UNIT н 10 50 Channel-to-case thermal resistance °C/W Rth(j-c) 3.1 2 10 40 K 0.40 0. 60 0.90 Channel-to-ambient thermal resistance °C/W Rth(j-a) 110 9.90 0

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# isc N-Channel MOSFET Transistor IRF

## IRFR120N, IIRFR120N

## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	100			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =250 µ A	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =5.6A			210	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			25	μA
V <sub>SD</sub>	Diode forward voltage	I <sub>s</sub> =5.5A, V <sub>GS</sub> = 0V			1.3	V

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